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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, LINbus, MMC/SD, SAI, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	112
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	640K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	169-UFBGA
Supplier Device Package	169-UFBGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l4r5aii6

1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32L4Rxxx microcontrollers.

This document should be read in conjunction with the STM32L4Rxxx reference manual (RM0432). The reference manual is available from the STMicroelectronics website www.st.com.

For information on the Arm®^(a) Cortex®-M4 core, please refer to the Cortex®-M4 Technical Reference Manual, available from the www.arm.com website.



arm

a. Arm is a registered trademark of Arm Limited (or its subsidiaries) in the US and/or elsewhere.

**Table 2. STM32L4R5xx, STM32L4R7xx and STM32L4R9xx
features and peripheral counts**

Peripheral	R5VI R5VG	R7VI R9VG	R9VI R9VG	R5QI R5QG	R5ZI R5ZG	R7ZI	R9ZI R9ZG	R5AI R5AG	R7AI	R9AI R9AG																				
Flash memory	1 Mbyte for xxxG devices 2 Mbyte for xxxL devices																													
SRAM	System	640 (192 + 64 + 384) Kbyte																												
	Backup	128 byte																												
External memory controller for static memories (FSMC)	Yes ⁽¹⁾		Yes																											
OctoSPI	2																													
Timers	Advanced control	2 (16-bit)																												
	General purpose	5 (16-bit) 2 (32-bit)																												
	Basic	2 (16-bit)																												
	Low-power	2 (16-bit)																												
	SysTick timer	1																												
	Watchdog timers (independent, window)	2																												
Comm. interfaces	SPI	3																												
	I ² C	4																												
	USART/UART	3																												
	UART	2																												
	LPUART	1																												
	SAI	2																												
	CAN	1																												
USB OTG FS		Yes																												
SDMMC		Yes																												
Digital filters for sigma-delta modulators	Yes (4 filters)																													
Number of channels	8																													
RTC	Yes																													
Tamper pins	3																													
Camera interface	Yes																													
Chrom-ART Accelerator™	Yes																													
Chrom-GRC™	No	Yes	No		Yes		No		Yes																					

Table 15. STM32L4Rxxx pin definitions (continued)

Pin number																Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions						
STM32L4R5xxx, STM32L4R7xxx								STM32L4R9xxx																			
	LQFP100	BGA132_SMPS	BGA132	LQFP144_SMPS	LQFP144	WL CSP144	UFBGA169_SMPS	UFBGA169	LQFP100	LQFP144	UFBGA144	WL CSP144_SMPS	WL CSP144	UFBGA169													
-	M4	M4	-	-	-	N4	N4	-	-	-	-	-	-	-	OPAMP_2_VINM	I	TT	-	-	-	-						
32	J5	J5	43	43	M10	L4	L4	30	40	M4	M10	M10	M4	M4	PA7	I/O	FT fla	-	TIM1_CH1N, TIM3_CH2, TIM8_CH1N, I2C3_SCL, SPI1_MOSI, OCTOSPI_M_P1_IO2, TIM17_CH1, EVENTOUT	OPAMP2_VINM, ADC1_IN12							
33	K5	K5	44	44	L9	H5	H5	31	41	L5	L9	L9	K4	PC4	I/O	FT_a	-	USART3_TX, OCTOSPI_M_P1_IO7, EVENTOUT	COMP1_INM, ADC1_IN13								
34	L5	L5	45	45	K8	J5	J5	-	-	K5	K8	K8	-	PC5	I/O	FT_a	-	SAI1_D3, USART3_RX, EVENTOUT	COMP1_INP, ADC1_IN14, WKUP5								
35	M5	M5	46	46	M9	K5	K5	32	42	M5	M9	M9	N4	PB0	I/O	TT_la	-	TIM1_CH2N, TIM3_CH3, TIM8_CH2N, SPI1_NSS, USART3_CK, OCTOSPI_M_P1_IO1, COMP1_OUT, SAI1_EXTCLK, EVENTOUT	OPAMP2_VOUT, ADC1_IN15								

Table 16. Alternate function AF0 to AF7⁽¹⁾ (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		OTG_FS/ SYS_AF	TIM1/2/5/8/L PTIM1	TIM1/2/3/4/ 5	SPI2/SAI1/I2C4/U SART2/OTG_FS/T IM1/8/OCTOSPIM _P1	I2C1/2/3/4/DC MI	SPI1/2/3/I2C4/DFS DM1/DCMI/OCTOS PIM_P1/2	SPI3/I2C3/DFS DM1/COMP1/O CTOSPIM_P2	USART1/2/3
Port H	PH0	-	-	-	-	-	-	-	-
	PH1	-	-	-	-	-	-	-	-
	PH2	-	-	-	OCTOSPIM_P1_IO4	-	-	-	-
	PH3	-	-	-	-	-	-	-	-
	PH4	-	-	-	-	I2C2_SCL	OCTOSPIM_P2_DQS	-	-
	PH5	-	-	-	-	I2C2_SDA	-	-	-
	PH6	-	-	-	-	I2C2_SMBA	OCTOSPIM_P2_CLK	-	-
	PH7	-	-	-	-	I2C3_SCL	-	-	-
	PH8	-	-	-	-	I2C3_SDA	OCTOSPIM_P2_IO3	-	-
	PH9	-	-	-	-	I2C3_SMBA	OCTOSPIM_P2_IO4	-	-
	PH10	-	-	TIM5_CH1	-	-	OCTOSPIM_P2_IO5	-	-
	PH11	-	-	TIM5_CH2	-	-	OCTOSPIM_P2_IO6	-	-
	PH12	-	-	TIM5_CH3	-	-	OCTOSPIM_P2_IO7	-	-
	PH13	-	-	-	TIM8_CH1N	-	-	-	-
	PH14	-	-	-	TIM8_CH2N	-	-	-	-
	PH15	-	-	-	TIM8_CH3N	-	OCTOSPIM_P2_IO6	-	-

Table 17. Alternate function AF8 to AF15⁽¹⁾ (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		UART4/5/ LPUART1/ CAN2	CAN1/TSC	OTG_FS/DCMI/ OCTOSPI_P1/P2	LCD	SDMMC/ COMP1/2/ FMC	SAI1/2	TIM2/15/16/17/ LPTIM2	EVENOUT
Port D	PD0	-	CAN1_RX	-	LCD_B4	FMC_D2	-	-	EVENTOUT
	PD1	-	CAN1_TX	-	LCD_B5	FMC_D3	-	-	EVENTOUT
	PD2	UART5_RX	TSC_SYNC	DCMI_D11	-	SDMMC1_CM D	-	-	EVENTOUT
	PD3	-	-	OCTOSPIM_P2_NCS	LCD_CLK	FMC_CLK	-	-	EVENTOUT
	PD4	-	-	OCTOSPIM_P1_IO4	-	FMC_NOE	-	-	EVENTOUT
	PD5	-	-	OCTOSPIM_P1_IO5	-	FMC_NWE	-	-	EVENTOUT
	PD6	-	-	OCTOSPIM_P1_IO6	LCD_DE	FMC_NWAIT	SAI1_SD_A	-	EVENTOUT
	PD7	-	-	OCTOSPIM_P1_IO7	-	FMC_NCE/FM C_NE1	-	-	EVENTOUT
	PD8	-	-	DCMI_HSYNC	LCD_R3	FMC_D13	-	-	EVENTOUT
	PD9	-	-	DCMI_PIXCLK	LCD_R4	FMC_D14	SAI2_MCLK_A	-	EVENTOUT
	PD10	-	TSC_G6_IO1	-	LCD_R5	FMC_D15	SAI2_SCK_A	-	EVENTOUT
	PD11	-	TSC_G6_IO2	-	LCD_R6	FMC_A16	SAI2_SD_A	LPTIM2_ETR	EVENTOUT
	PD12	-	TSC_G6_IO3	-	LCD_R7	FMC_A17	SAI2_FS_A	LPTIM2_IN1	EVENTOUT
	PD13	-	TSC_G6_IO4	-	-	FMC_A18	-	LPTIM2_OUT	EVENTOUT
	PD14	-	-	-	LCD_B2	FMC_D0	-	-	EVENTOUT
	PD15	-	-	-	LCD_B3	FMC_D1	-	-	EVENTOUT



5 Memory mapping

Figure 23. STM32L4R5xx, STM32L4R7xx and STM32L4R9xx memory map

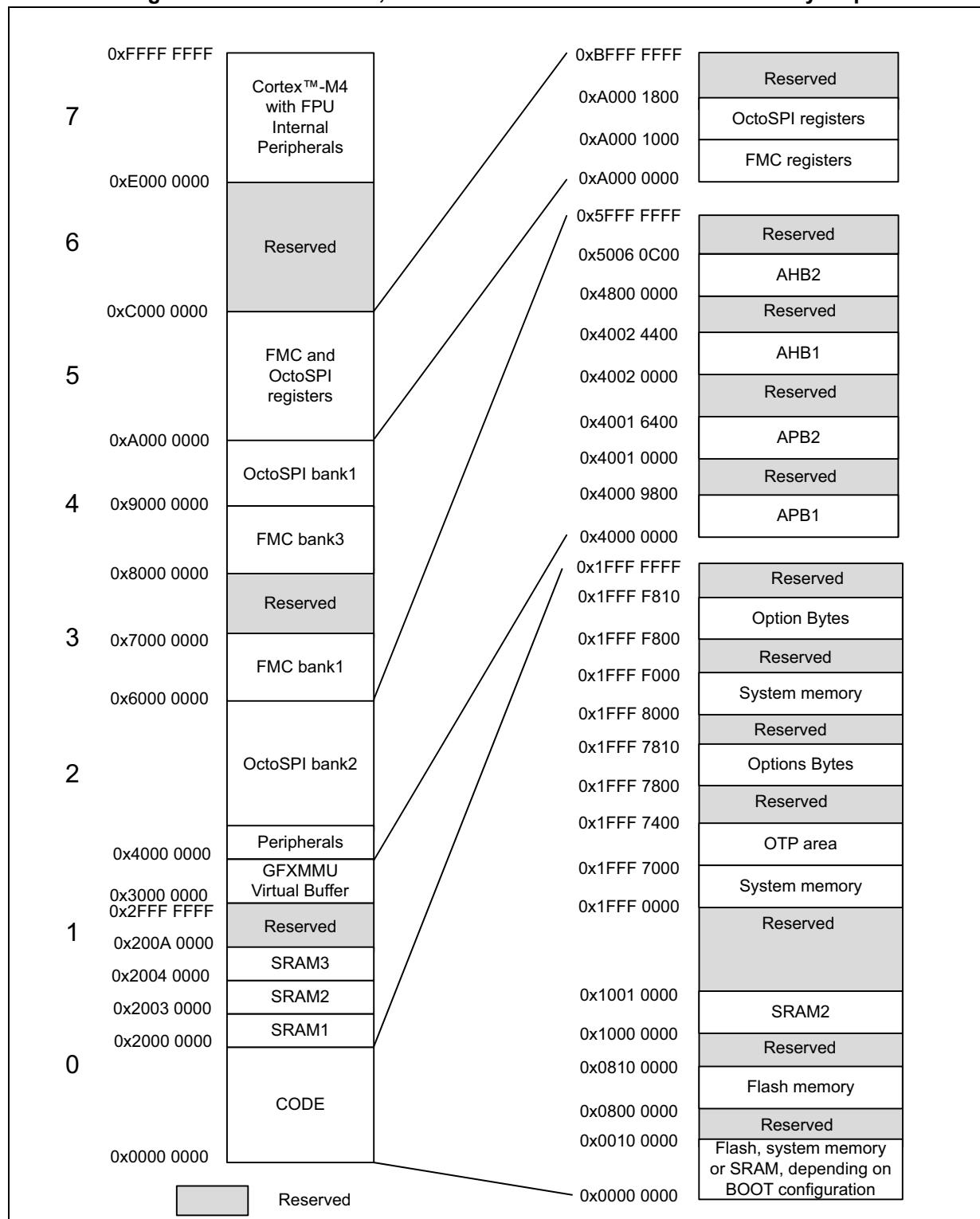


Table 53. Low-power mode wakeup timings⁽¹⁾ (continued)

Symbol	Parameter	Conditions		Typ	Max	Unit
t_{WUSTBY}	Wakeup time from Standby mode to Run mode	Range 1	Wakeup clock MSI = 8 MHz	30.7	47.8	μs
			Wakeup clock MSI = 4 MHz	40.4	55.6	
t_{WUSTBY_SRAM2}	Wakeup time from Standby with SRAM2 to Run mode	Range 1	Wakeup clock MSI = 8 MHz	32.1	49.1	μs
			Wakeup clock MSI = 4 MHz	41.5	55.5	
t_{WUSHDN}	Wakeup time from Shutdown mode to Run mode	Range 1	Wakeup clock MSI = 4 MHz	265.0	339.4	

1. Guaranteed by characterization results.

Table 54. Regulator modes transition times⁽¹⁾

Symbol	Parameter	Conditions	Typ	Max	Unit
$t_{WULPRUN}$	Wakeup time from Low-power run mode to Run mode ⁽²⁾	Code run with MSI 2 MHz	5	7	μs
t_{VOST}	Regulator transition time from Range 2 to Range 1 or Range 1 to Range 2 ⁽³⁾		20	40	

1. Guaranteed by characterization results.

2. Time until REGLPF flag is cleared in PWR_SR2.

3. Time until VOSF flag is cleared in PWR_SR2.

Table 55. Wakeup time using USART/LPUART⁽¹⁾

Symbol	Parameter	Conditions	Typ	Max	Unit
$t_{WUUSART}$ $t_{WULPUART}$	Wakeup time needed to calculate the maximum USART/LPUART baudrate allowing to wakeup up from stop mode when USART/LPUART clock source is HSI	Stop mode 0	-	1.7	μs
		Stop mode 1/2	-	8.5	

1. Guaranteed by characterization results.

Table 61. MSI oscillator characteristics⁽¹⁾ (continued)

Symbol	Parameter	Conditions			Min	Typ	Max	Unit
$I_{DD(MSI)}^{(6)}$	MSI oscillator power consumption	MSI and PLL mode	Range 0	-	-	0.6	1	μA
			Range 1	-	-	0.8	1.2	
			Range 2	-	-	1.2	1.7	
			Range 3	-	-	1.9	2.5	
			Range 4	-	-	4.7	6	
			Range 5	-	-	6.5	9	
			Range 6	-	-	11	15	
			Range 7	-	-	18.5	25	
			Range 8	-	-	62	80	
			Range 9	-	-	85	110	
			Range 10	-	-	110	130	
			Range 11	-	-	155	190	

1. Guaranteed by characterization results.
2. This is a deviation for an individual part once the initial frequency has been measured.
3. Sampling mode means Low-power run/Low-power sleep modes with Temperature sensor disable.
4. Average period of MSI @48 MHz is compared to a real 48 MHz clock over 28 cycles. It includes frequency tolerance + jitter of MSI @48 MHz clock.
5. Only accumulated jitter of MSI @48 MHz is extracted over 28 cycles.
For next transition: min. and max. jitter of 2 consecutive frame of 28 cycles of the MSI @48 MHz, for 1000 captures over 28 cycles.
For paired transitions: min. and max. jitter of 2 consecutive frame of 56 cycles of the MSI @48 MHz, for 1000 captures over 56 cycles.
6. Guaranteed by design.

Figure 34. Typical current consumption versus MSI frequency

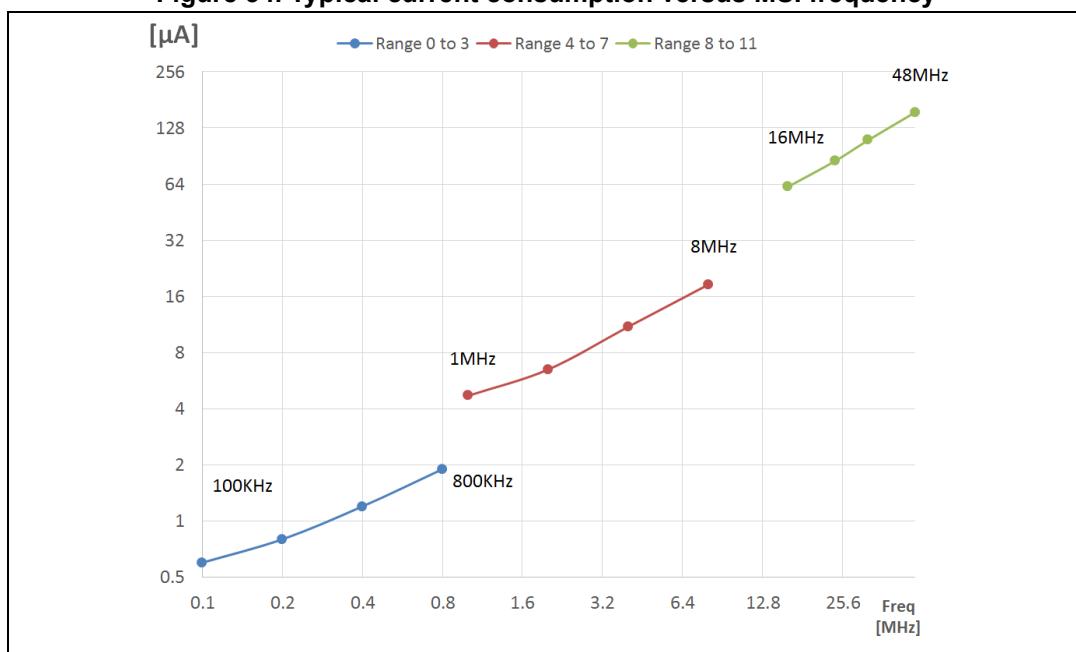
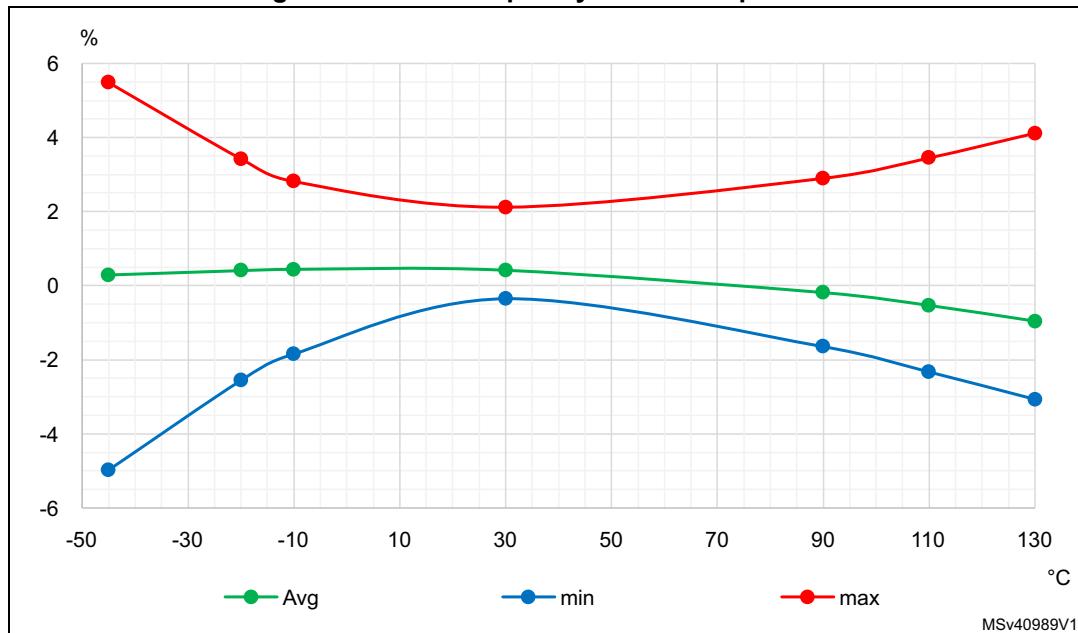


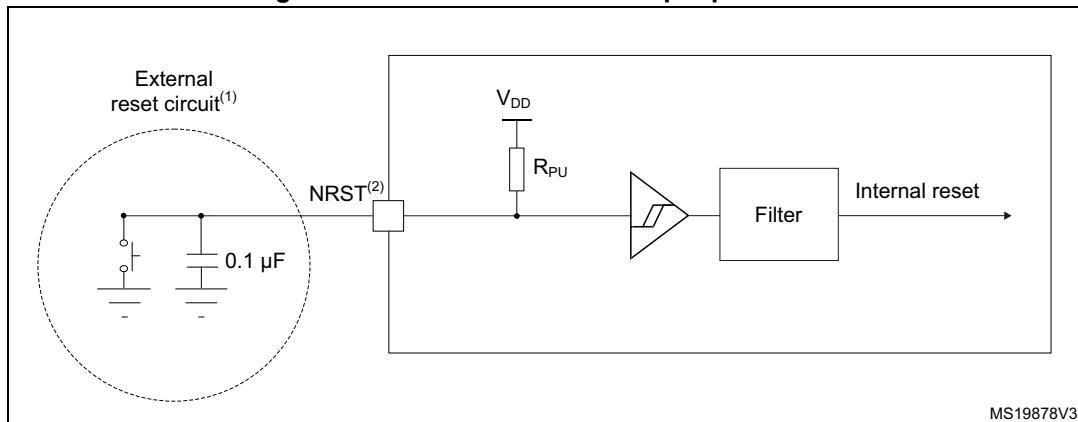
Figure 35. HSI48 frequency versus temperature**Low-speed internal (LSI) RC oscillator****Table 63. LSI oscillator characteristics⁽¹⁾**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSI}	LSI Frequency	$V_{DD} = 3.0 \text{ V}, T_A = 30 \text{ }^\circ\text{C}$	31.04	-	32.96	kHz
		$V_{DD} = 1.62 \text{ to } 3.6 \text{ V}, T_A = -40 \text{ to } 125 \text{ }^\circ\text{C}$	29.5	-	34	
$t_{SU(LSI)}^{(2)}$	LSI oscillator start-up time	-	-	80	130	μs
$t_{STAB(LSI)}^{(2)}$	LSI oscillator stabilization time	5% of final frequency	-	125	180	μs
$I_{DD(LSI)}^{(2)}$	LSI oscillator power consumption	-	-	110	180	nA

1. Guaranteed by characterization results.

2. Guaranteed by design.

Figure 40. Recommended NRST pin protection



MS19878V3

1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in [Table 79: NRST pin characteristics](#). Otherwise the reset will not be taken into account by the device.
3. The external capacitor on NRST must be placed as close as possible to the device.

6.3.19 Extended interrupt and event controller input (EXTI) characteristics

The pulse on the interrupt input must have a minimal length in order to guarantee that it is detected by the event controller.

Table 80. EXTI input characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PLEC	Pulse length to event controller	-	20	-	-	ns

1. Guaranteed by design.

6.3.20 Analog switches booster

Table 81. Analog switches booster characteristics⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
V_{DD}	Supply voltage	1.62	-	3.6	V
$t_{SU(BOOST)}$	Booster startup time	-	-	240	μs
$I_{DD(BOOST)}$	Booster consumption for $1.62 \text{ V} \leq V_{DD} \leq 2.0 \text{ V}$	-	-	250	μA
	Booster consumption for $2.0 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$	-	-	500	
	Booster consumption for $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	-	900	

1. Guaranteed by design.

Table 86. ADC accuracy - limited test conditions 3⁽¹⁾⁽²⁾⁽³⁾

Symbol	Parameter	Conditions ⁽⁴⁾				Min	Typ	Max	Unit	
ET	Total unadjusted error	ADC clock frequency ≤ 80 MHz, Sampling rate ≤ 5.33 Msps, 1.65 V ≤ V _{DDA} = V _{REF+} ≤ 3.6 V, Voltage scaling Range 1	Single ended	Fast channel (max speed)	-	5.5	7.5		LSB	
				Slow channel (max speed)	-	4.5	6.5			
			Differential	Fast channel (max speed)	-	4.5	7.5			
				Slow channel (max speed)	-	4.5	5.5			
	Offset error		Single ended	Fast channel (max speed)	-	2	5			
				Slow channel (max speed)	-	2.5	5			
			Differential	Fast channel (max speed)	-	2	3.5			
				Slow channel (max speed)	-	2.5	3			
	Gain error		Single ended	Fast channel (max speed)	-	4.5	7			
				Slow channel (max speed)	-	3.5	6			
			Differential	Fast channel (max speed)	-	3.5	4			
				Slow channel (max speed)	-	3.5	5			
ED	Differential linearity error		Single ended	Fast channel (max speed)	-	1.2	1.5		bits	
				Slow channel (max speed)	-	1.2	1.5			
			Differential	Fast channel (max speed)	-	1	1.2			
				Slow channel (max speed)	-	1	1.2			
	Integral linearity error		Single ended	Fast channel (max speed)	-	3	3.5			
				Slow channel (max speed)	-	2.5	3.5			
			Differential	Fast channel (max speed)	-	2	2.5			
				Slow channel (max speed)	-	2	2.5			
	ENOB		Single ended	Fast channel (max speed)	10	10.4	-			
				Slow channel (max speed)	10	10.4	-			
			Differential	Fast channel (max speed)	10.6	10.7	-			
				Slow channel (max speed)	10.6	10.7	-			
SINAD	Signal-to-noise and distortion ratio		Single ended	Fast channel (max speed)	62	64	-		dB	
				Slow channel (max speed)	62	64	-			
			Differential	Fast channel (max speed)	65	66	-			
				Slow channel (max speed)	65	66	-			
	SNR		Single ended	Fast channel (max speed)	63	65	-			
				Slow channel (max speed)	63	65	-			
			Differential	Fast channel (max speed)	66	67	-			
				Slow channel (max speed)	66	67	-			

Table 87. ADC accuracy - limited test conditions 4⁽¹⁾⁽²⁾⁽³⁾ (continued)

Symbol	Parameter	Conditions ⁽⁴⁾			Min	Typ	Max	Unit
THD	Total harmonic distortion	ADC clock frequency ≤ 26 MHz, 1.65 V ≤ V _{DDA} = VREF+ ≤ 3.6 V, Voltage scaling Range 2	Single ended	Fast channel (max speed)	-	-71	-69	dB
				Slow channel (max speed)	-	-71	-69	
			Differential	Fast channel (max speed)	-	-73	-72	
				Slow channel (max speed)	-	-73	-72	

1. Guaranteed by design.
2. ADC DC accuracy values are measured after internal calibration.
3. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
4. The I/O analog switch voltage booster is enable when V_{DDA} < 2.4 V (BOOSTEN = 1 in the SYSCFG_CFG1 when V_{DDA} < 2.4 V). It is disable when V_{DDA} ≥ 2.4 V. No oversampling.

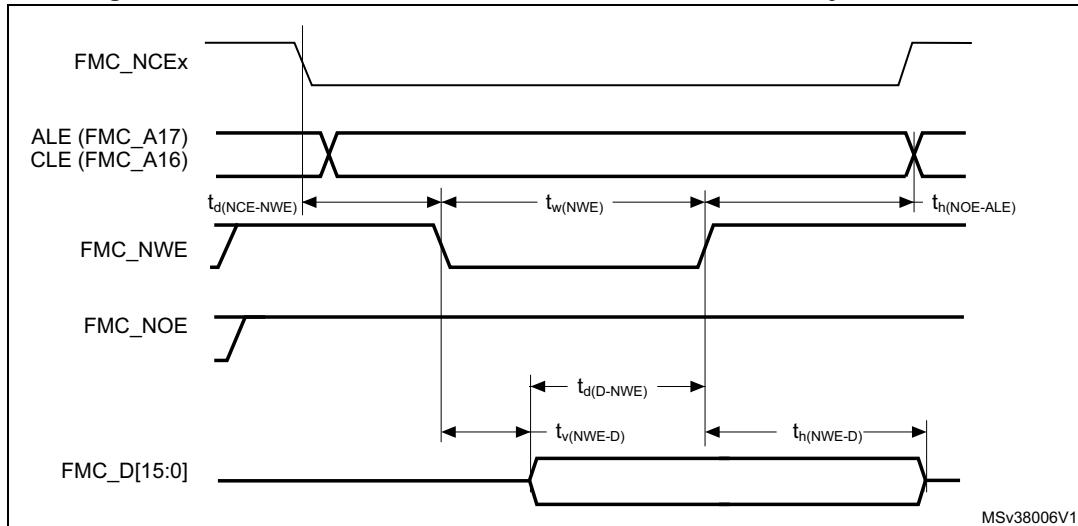
conditions summarized in [Table 22: General operating conditions](#), with the following configuration:

- Output speed is set to OSPEEDR_Y[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5 x V_{DD}

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output alternate function characteristics (CK,SD,FS).

Table 102. SAI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCLK}	SAI Main clock output	-	-	50	MHz
f_{CK}	SAI clock frequency ⁽²⁾	Master transmitter 2.7 V ≤ V_{DD} ≤ 3.6 V Voltage Range 1	-	23.5	MHz
		Master transmitter 1.71 V ≤ V_{DD} ≤ 3.6 V Voltage Range 1	-	16	
		Master receiver Voltage Range 1	-	16	
		Slave transmitter 2.7 V ≤ V_{DD} ≤ 3.6 V Voltage Range 1	-	26	
		Slave transmitter 1.71 V ≤ V_{DD} ≤ 3.6 V Voltage Range 1	-	20	
		Slave receiver Voltage Range 1	-	25	
		Voltage Range 2	-	13	
		1.08 V ≤ V_{DD} ≤ 1.32 V	-	9	
$t_{V(FS)}$	FS valid time	Master mode 2.7 V ≤ V_{DD} ≤ 3.6 V	-	21	ns
		Master mode 1.71 V ≤ V_{DD} ≤ 3.6 V	-	30	
$t_{h(FS)}$	FS hold time	Master mode	10	-	ns
$t_{su(FS)}$	FS setup time	Slave mode	1.5	-	ns
$t_{h(FS)}$	FS hold time	Slave mode	2.5	-	ns
$t_{su(SD_A_MR)}$	Data input setup time	Master receiver	1	-	ns
$t_{su(SD_B_SR)}$		Slave receiver	1.5	-	
$t_{h(SD_A_MR)}$	Data input hold time	Master receiver	6.5	-	ns
$t_{h(SD_B_SR)}$		Slave receiver	2.5	-	
$t_{v(SD_B_ST)}$	Data output valid time	Slave transmitter (after enable edge) 2.7 V ≤ V_{DD} ≤ 3.6 V	-	19	ns
		Slave transmitter (after enable edge) 1.71 V ≤ V_{DD} ≤ 3.6 V	-	25	
		Slave transmitter (after enable edge) 1.08 V < V_{DD} < 1.32 V	-	50	
$t_{h(SD_B_ST)}$	Data output hold time	Slave transmitter (after enable edge)	10	-	ns

Figure 61. NAND controller waveforms for common memory write access**Table 118. Switching characteristics for NAND Flash read cycles⁽¹⁾⁽²⁾**

Symbol	Parameter	Min	Max	Unit
$T_{w(\text{NOE})}$	FMC_NOE low width	$4T_{\text{HCLK}}-0.5$	$4T_{\text{HCLK}}+0.5$	ns
$T_{su(\text{D-NOE})}$	FMC_D[15-0] valid data before FMC_NOE high	14	-	
$T_{h(\text{NOE-D})}$	FMC_D[15-0] valid data after FMC_NOE high	0	-	
$T_{d(\text{NCE-NOE})}$	FMC_NCE valid before FMC_NOE low	-	$3T_{\text{HCLK}}+1$	
$T_{h(\text{NOE-ALE})}$	FMC_NOE high to FMC_ALE invalid	$3T_{\text{HCLK}}-0.5$	-	

1. CL = 30 pF.

2. Guaranteed by characterization results.

Table 119. Switching characteristics for NAND Flash write cycles⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$T_{w(\text{NWE})}$	FMC_NWE low width	$2T_{\text{HCLK}}-0.5$	$4T_{\text{HCLK}}+0.5$	ns
$T_{v(\text{NWE-D})}$	FMC_NWE low to FMC_D[15-0] valid	5	-	
$T_{h(\text{NWE-D})}$	FMC_NWE high to FMC_D[15-0] invalid	$2T_{\text{HCLK}}-1$	-	
$T_{d(\text{D-NWE})}$	FMC_D[15-0] valid before FMC_NWE high	$5T_{\text{HCLK}}-1$	-	
$T_{d(\text{NCE-NWE})}$	FMC_NCE valid before FMC_NWE low	-	$3T_{\text{HCLK}}-1$	
$T_{h(\text{NWE-ALE})}$	FMC_NWE high to FMC_ALE invalid	$3T_{\text{HCLK}}-0.5$	-	

1. CL = 30 pF.

2. Guaranteed by characterization results.

6.3.32 OctoSPI characteristics

Unless otherwise specified, the parameters given in [Table 120](#), [Table 121](#) and [Table 122](#) for OctoSPI are derived from tests performed under the ambient temperature, f_{AHB} frequency

Figure 65. OctoSPI Hyperbus read

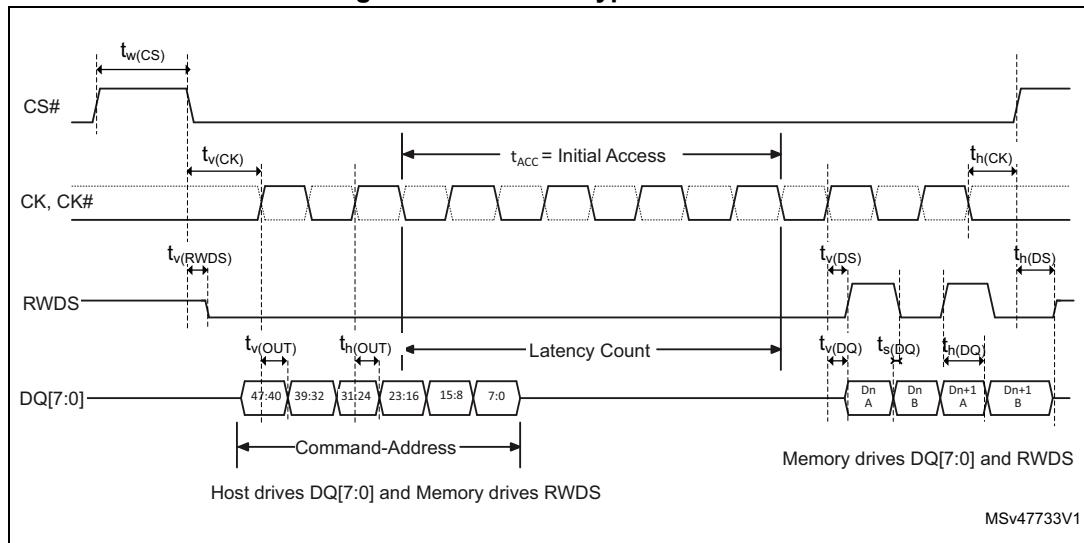
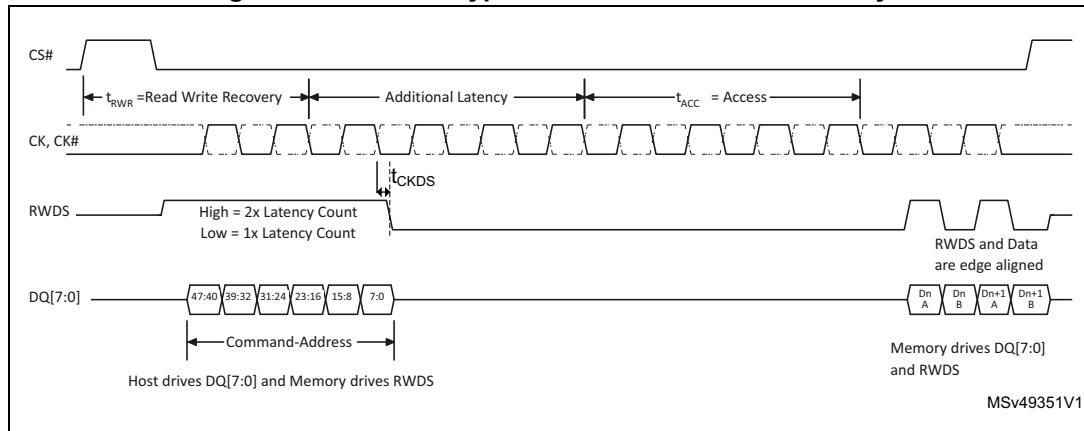


Figure 66. OctoSPI Hyperbus read with double latency



**Table 125. Dynamics characteristics:
SD / eMMC characteristics at VDD = 2.7 V to 3.6 V⁽¹⁾ (continued)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
CMD, D inputs (referenced to CK) in eMMC legacy/SDR/DDR and SD HS/SDR⁽²⁾/DDR⁽²⁾ mode						
tISU	Input setup time HS	-	1.5	-	-	ns
tIHD	Input hold time HS	-	2	-	-	
CMD, D outputs (referenced to CK) in eMMC legacy/SDR/DDR and SD HS/SDR⁽²⁾/DDR⁽²⁾ mode						
tOV	Output valid time HS	-	-	5	6.5	ns
tOH	Output hold time HS	-	4	-	-	
CMD, D inputs (referenced to CK) in SD default mode						
tISUD	Input setup time SD	-	1.5	-	-	ns
tIHD	Input hold time SD	-	2	-	-	
CMD, D outputs (referenced to CK) in SD default mode						
tOVD	Output valid default time SD	-	-	1	2.5	ns
tOHD	Output hold default time SD	-	0	-	-	

1. Guaranteed by characterization results.
2. For SD 1.8 V support, an external voltage converter is needed.

**Table 126. Dynamics characteristics:
eMMC characteristics at VDD = 1.71 V to 1.9 V⁽¹⁾⁽²⁾**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
fPP	Clock frequency in data transfer mode	-	0	-	52	MHz
-	SDIO_CK/fPCLK2 frequency ratio	-	-	-	8/3	-
tW(CKL)	Clock low time	fpp = 52 MHz	8.5	9.5	-	ns
tW(CKH)	Clock high time	fpp = 52 MHz	8.5	9.5	-	
CMD, D inputs (referenced to CK) in eMMC mode						
tISU	Input setup time HS	-	0.5	-	-	ns
tIH	Input hold time HS	-	4.5	-	-	
CMD, D outputs (referenced to CK) in eMMC mode						
tOV	Output valid time HS	-	-	6	7.4	ns
tOH	Output hold time HS	-	4	-	-	

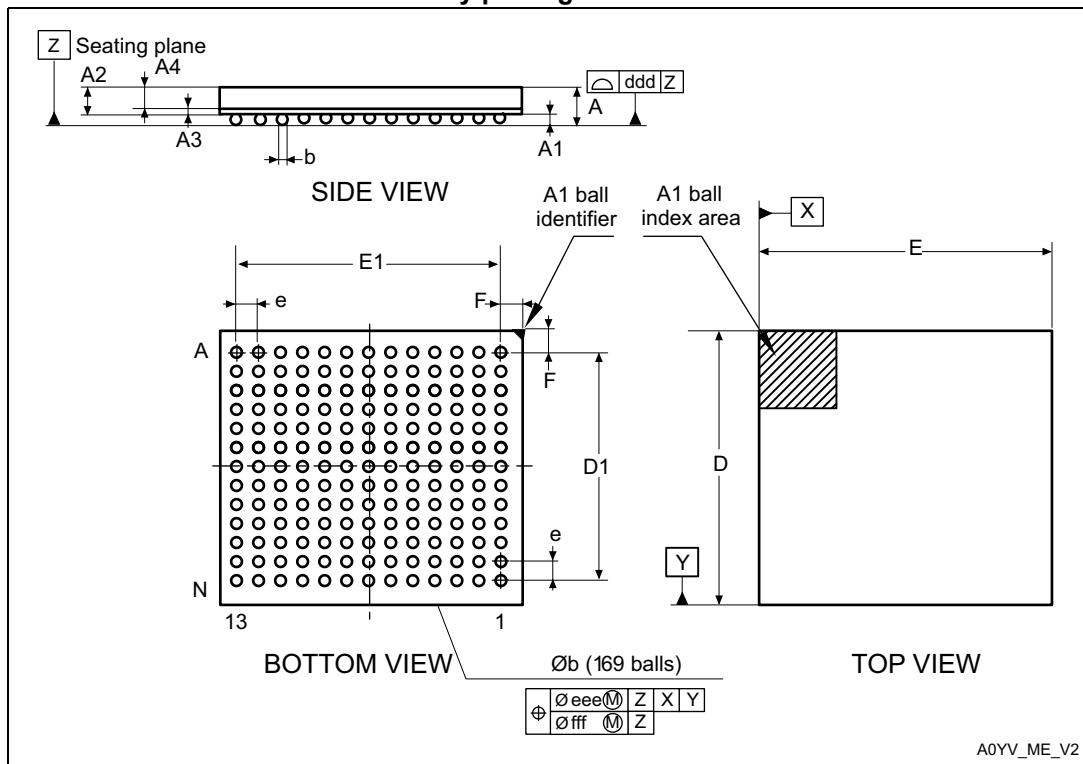
1. Guaranteed by characterization results.
2. Cload = 20 pF.

7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.
ECOPACK® is an ST trademark.

7.1 UFBGA169 package information

Figure 72. UFBGA169 - 169-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package outline



1. Drawing is not to scale.

Table 127. UFBGA169 - 169-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.460	0.530	0.600	0.0181	0.0209	0.0236
A1	0.050	0.080	0.110	0.0020	0.0031	0.0043
A2	0.400	0.450	0.500	0.0157	0.0177	0.0197
A3	-	0.130	-	-	0.0051	-
A4	0.270	0.320	0.370	0.0106	0.0126	0.0146

Table 134. UFBGA132 - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
e	-	0.500	-	-	0.0197	-
Z	-	0.750	-	-	0.0295	-
ddd	-	0.080	-	-	0.0031	-
eee	-	0.150	-	-	0.0059	-
fff	-	0.050	-	-	0.0020	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 86. UFBGA132 - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package recommended footprint

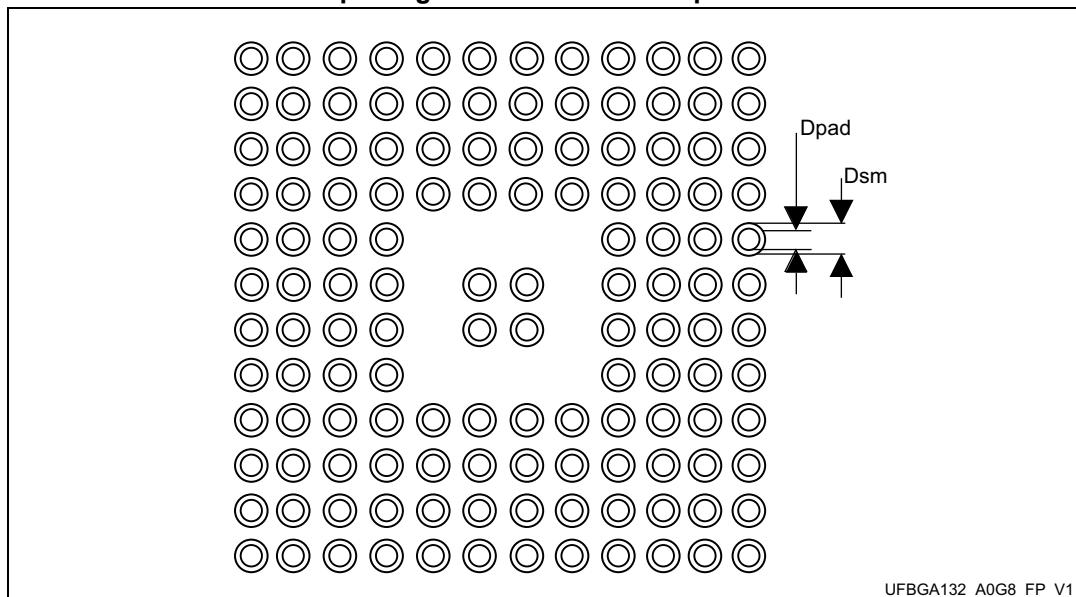


Table 135. UFBGA132 recommended PCB design rules (0.5 mm pitch BGA)

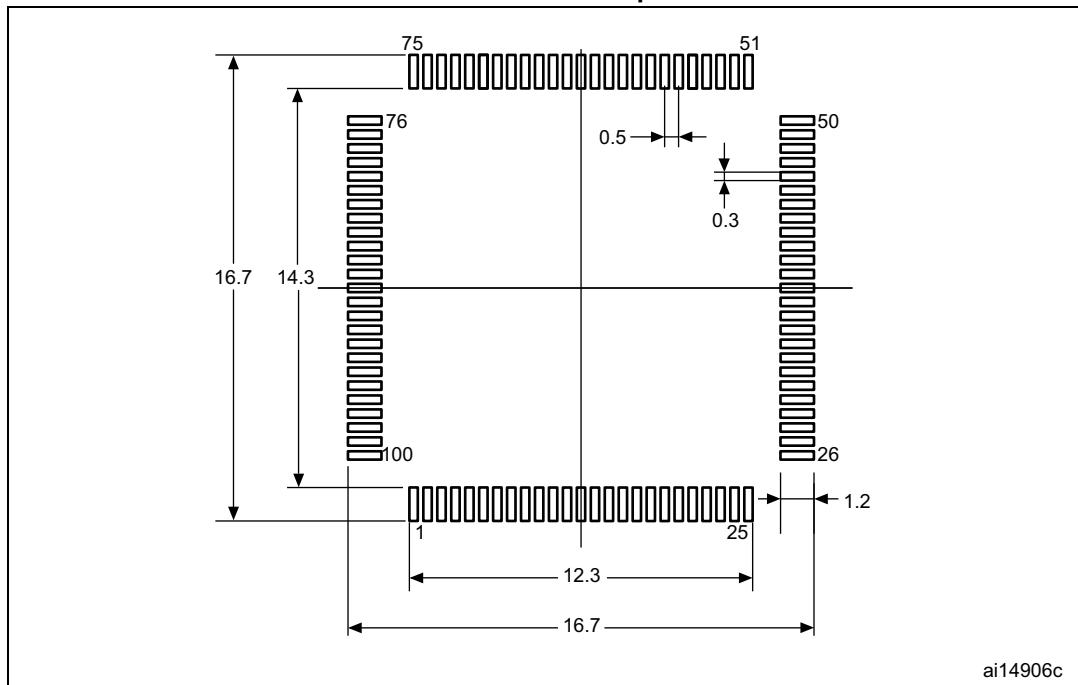
Dimension	Recommended values
Pitch	0.5 mm
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm
Ball diameter	0.280 mm

Table 136. LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 89. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat recommended footprint



1. Dimensions are expressed in millimeters.

LQFP100 device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.